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(54) **MONOLITHIC MICROWAVE INTEGRATED CIRCUIT (MMIC) CASCODE CONNECTED TRANSISTOR CIRCUIT**

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See application file for complete search history.

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(57)

ABSTRACT

A cascode transistor circuit having an active region, the active region having a source, a drain, a floating source/drain, a first gate disposed between the source and the floating source/drain and a second gate disposed between the floating source/drain and the drain. A first gate pad is displaced from the active region and is electrically connected to the first gate and a second gate pad is displaced from the active region and is electrically connected to the second gate. The first and the second gate pads are disposed on opposite sides of the active region.

7 Claims, 9 Drawing Sheets

